

Silicon NPN Power Transistors

BU536

DESCRIPTION

- With TO-3 package
- High voltage
- Fast switching speed

APPLICATIONS

- For color TV horizontal deflection circuits.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1100	V
V_{CEO}	Collector-emitter voltage	Open base	480	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak	$t_p < 5ms$	15	A
P_T	Total power dissipation	$T_C = 25\square$	62	W
T_j	Junction temperature		175	$\square$
T_{stg}	Storage temperature		-65~175	$\square$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-C}$	Thermal resistance junction to case	1.0	$\square/W$

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA$; $I_B=0$;	480			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10mA$; $I_C=0$;	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4A$; $I_B=0.8A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4A$; $I_B=0.8A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=1100V$; $I_E=0$			1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=1A$; $V_{CE}=5V$	10			
h_{FE-2}	DC current gain	$I_C=4A$; $V_{CE}=5V$	6.5			

PACKAGE OUTLINE

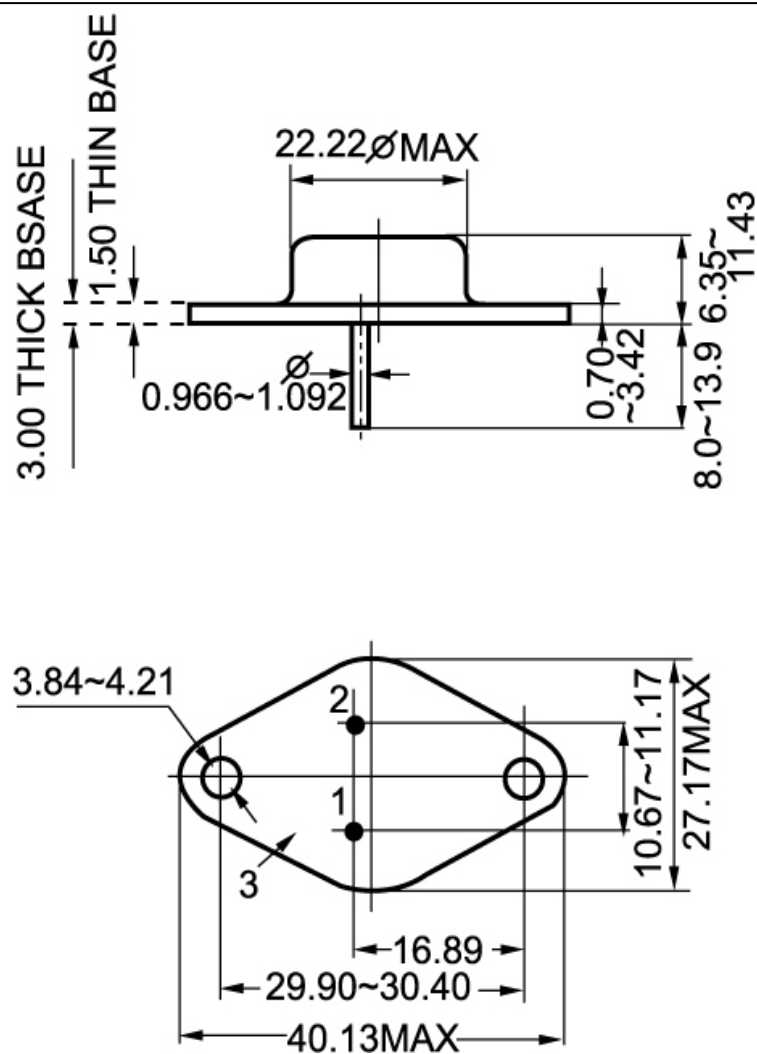


Fig.2 Outline dimensions